

### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

## IRFB4137, IIRFB4137

### FEATURES

- Static drain-source on-resistance: RDs(on) ≤69mΩ
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

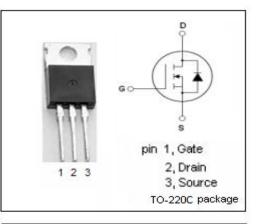
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply

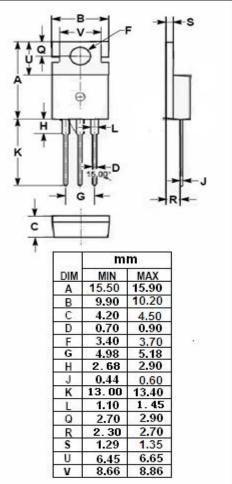
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	300	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous	38	A
I <sub>DM</sub>	Drain Current-Single Pulsed 152		А
P <sub>D</sub>	Total Dissipation @T <sub>c</sub> =25°C	341	W
Tj	Max. Operating Junction Temperature	175	°C
T <sub>stg</sub>	Storage Temperature	-55~175	°C

#### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.44	°C/W
Rth(ch-a)	Channel-to-ambient thermal resistance	62	°C/W







# isc N-Channel MOSFET Transistor IRFB413

## IRFB4137, IIRFB4137

### ELECTRICAL CHARACTERISTICS

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A	300			v
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =250 μ A	3		5	v
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =24A			69	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =300V; V <sub>GS</sub> = 0V			20	μA
V <sub>SD</sub>	Diode forward voltage	Is=24A; V <sub>GS</sub> = 0V			1.3	V

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